

CLAIMS

1. A semiconductor device substrate comprised of a core substrate on at least one surface of which interconnect patterns are formed via a resin layer, wherein

the core substrate is formed by a material having a heat expansion coefficient closer to a semiconductor chip than resin layers and the interconnect patterns inside the substrate, and

a resin layer forming an outermost layer of the substrate is formed using a material having at least one of a higher strength and a higher elongation than a resin material used for inner resin layers in the substrate,

thereby cracking, deformation, and other problems arising in the substrate due to the thermal stress occurring between the core substrate and the resin layers in the substrate and interconnect patterns being prevented.

2. A semiconductor device substrate as set forth in claim 1, wherein a resin layer under a resin layer forming an outermost layer of the substrate is made of a resin material having at least one of a higher strength and higher elongation than the resin material of a resin layer used further inside the substrate.

3. A semiconductor device substrate as set forth in claim 1 or 2, wherein the resin material having at least one of a higher strength and higher elongation is a resin material having a fracture strength of at least 90 MPa and elongation of at least 10%.